

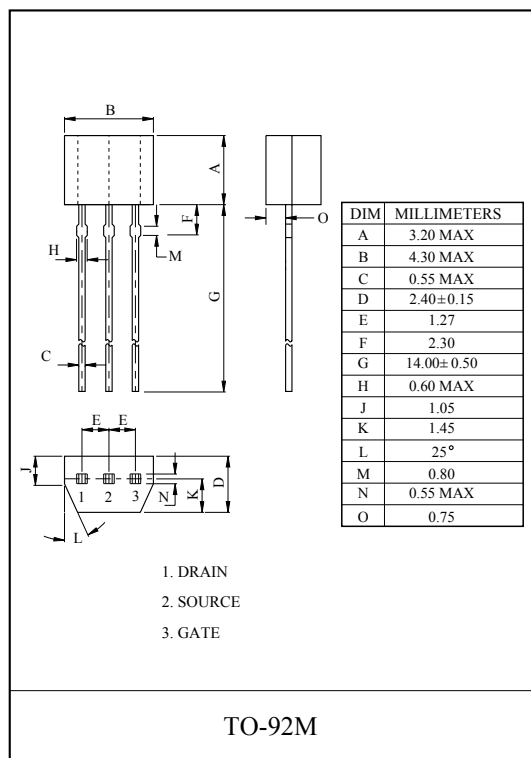
HIGH FREQUENCY APPLICATION.
VHF BAND AMPLIFIER APPLICATION.

FEATURES

- Low Noise Figure.
: $NF=2.5dB(Typ.) (f=100MHz)$.
- High Forward Transfer Admittance.
: $|y_{fs}|=9mS(Typ.)$.
- Extremely Low Reverse Transfer Capacitance.
: $C_{rss}=0.1pF(Typ.)$

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate-Drain Voltage	V_{GDO}	-18	V
Gate-Current	I_G	10	mA
Drain Power Dissipation	P_D	400	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 ~ 150	℃

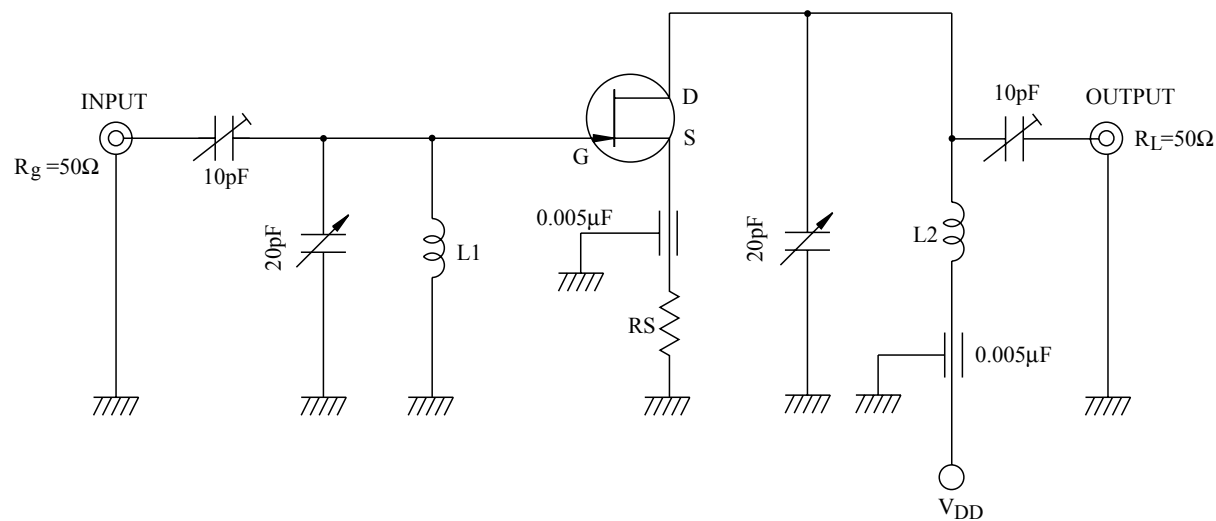


ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GSS}	$V_{GS}=-0.5V, V_{DS}=0$	-	-	-10	nA
Gate-Drain Breakdown Voltage	$V_{(BR)GDO}$	$I_G=-100\mu A$	-18	-	-	V
Drain Current	$I_{DSS} (Note)$	$V_{DS}=10V, V_{GS}=0V$	1.0	-	15.0	mA
Gate-Source Cut-off Voltage	$V_{GS(OFF)}$	$V_{DS}=10V, I_D=1\mu A$	-0.4	-	-4.0	V
Foward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, V_{GS}=0, f=1kHz$	-	9.0	-	mS
Reverse Transfer Capacitance	C_{rss}	$V_{GD}=-10V, f=1MHz$	-	0.10	0.15	pF
Power Gain	G_{ps}	$V_{DD}=10V, f=100MHz (Fig.)$	-	18	-	dB
Noise Figure	NF	$V_{DD}=10V, f=100MHz (Fig.)$	-	2.5	3.5	dB

Note : I_{DSS} Classification O:1.0 ~ 3.0, Y:2.5 ~ 6.0, GR:5.0 ~ 10.0, BL:9.0 ~ 15.0

Fig. 100MHz G_{PS} , NF TEST CIRCUIT



L1 : 0.8mmΦ Ag PLATED Cu WIRE , 3 TURNS , 10mm ID , 10mm LENGTH.
L1 : 0.8mmΦ Ag PLATED Cu WIRE , 3.5 TURNS , 10mm ID , 10mm LENGTH.

KTK161 is measured at each group by changing R_S .

Group	$R_S(\Omega)$
KTK161-O	0
KTK161-Y	$18\Omega \pm 5\%$
KTK161-GR	$100\Omega \pm 5\%$
KTK161-BL	$200\Omega \pm 5\%$

